

P-Channel 20-V (D-S) MOSFET

Description

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low rDS(on) and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

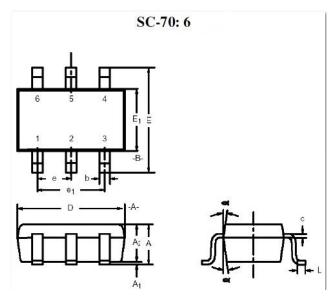
- Low rDS(on) provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-6 saves board space
- · Fast switching speed
- · High performance trench technology
- · RoHS compliant package

Packing & Order Information

3,000/Reel

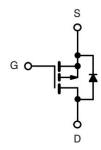


RoHS COMPLIANT



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.90	_	1.10	0.035	2-0	0.043	
Α1	_	-	0.10	-	21—12	0.004	
A ₂	0.80	-	1.00	0.031	5. - .5	0.039	
b	0.15)	0.30	0.006	82 83	0.012	
С	0.10	-	0.25	0.004	82—84	0.010	
D	1.80	2.00	2.20	0.071	0.079	0.087	
Е	1.80	2.10	2.40	0.071	0.083	0.094	
E ₁	1.15	1.25	1.35	0.045	0.049	0.053	
е	0.65BSC			0.026BSC			
e ₁	1.20	1.30	1.40	0.047	0.051	0.055	
L	0.10	0.20	0.30	0.004	0.008	0.012	
4	7°Nom			7°Nom			

Graphic symbol





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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)					
Symbol	Parameter	Value	Unit		
V_{DS}	Drain-Source Voltage	-20	V		
V _{GS}	Gate-Source Voltage	±8	V		
I _D	Continuous Drain Current ^a (T _A =25°C)	-3.7	А		
	Continuous Drain Current ^a (T _A =70°C)	-3.0	Α		
I _{DM}	Pulsed Drain Current ^b	-10	А		
I _S	Continuous Source Current (Diode Conduction) ^a	±1.4	А		
	Power Dissipation ^a (T _A =25°C)	1.56	W		
P_D	Power Dissipation ^a (T _A =70°C)	0.81	W		
T _J /T _{STG}	Operating Junction and Storage Temperature	-55 to +150	°C		

Thermal Resistance Ratings						
Symbol	Parameter	Maximum	Units			
R _{THJA}	Maximum Junction-to-Ambient C/W ^a (t <= 5 sec)	80	°C/W			
	Maximum Junction-to-Ambient C/W ^a (Steady-State)	125	C/VV			

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Static						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
$V_{GS(th)}$		$V_{DS} = V_{GS}$, I_D =-250 μ A	-0.4			V
I _{GSS}	Gate-Body Leakage	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 8 \text{ V}$			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16 V , V _{GS} = 0 V			-1	uA
		$V_{DS} = -16 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_{J} = 55^{\circ}\text{C}$			-10	u/\
$I_{D(on)}$	On-State Drain Current ^A	$V_{DS} = -5 \text{ V}, V_{Gs} = -4.5 \text{ V}$	-5			Α
I _{DS(on)}	Drain-Source On-Resistance ^A	$V_{GS} = -4.5 \text{ V}, I_D = -3.7 \text{ A}$			79	
		$V_{GS} = -2.5 \text{ V}, I_{D} = -3.1 \text{ A}$			110	mΩ
		$V_{GS} = -1.8 \text{ V}, I_{D} = -2.6 \text{ A}$			160	
g _{fs}	Forward Tranconductance ^A	$V_{DS} = -5 \text{ V}, I_{D} = -1.25 \text{ A}$		9		S
V _{SD}	Diode Forward Voltage	I _S = -0.46 V, V _{GS} = 0 V		-0.65		V



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Dynamic ^b							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10 \text{ V} , I_L = -1 \text{ A},$ $V_{GEN} = -4.5 \text{ V} , R_G = 6 \Omega$		10		ns	
t _r	Rise Time			9		ns	
$t_{d(off)}$	Turn-Off Delay Time			27		ns	
tf	Fall Time			11		ns	
Q _g	Total Gate Charge	$V_{DS} = -10 \text{ V}$, $I_{D} = -3.7 \text{ A}$, $V_{GS} = -4.5 \text{ V}$		7.2		nC	
Q_{gs}	Gate-Source Charge			1.7		nC	
Q_{gd}	Gate-Drain Charge			1.5		nC	

Notes:

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Repetitive rating, pulse width limited by junction temperature.



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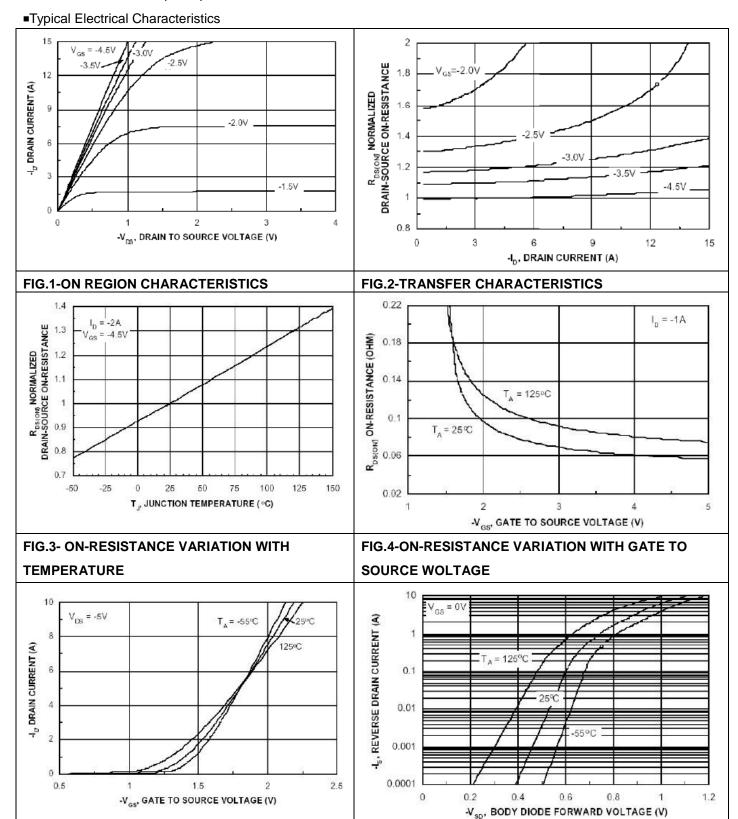


FIG.5-TRANSFER CHARACTERISTICS

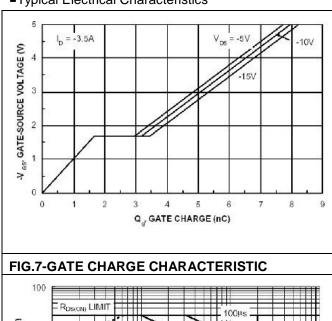
FIG.6-BODY DIODE FORWARD VOLTAGE VARIATION

WITH SOURCE CURRENT AND TEMPERATURE



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■Typical Electrical Characteristics



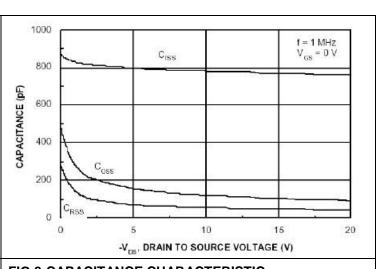


FIG.7-GATE CHARGE CHARACTERISTIC 100 R_{DSI(OR)} LIMIT 100ms 100ms

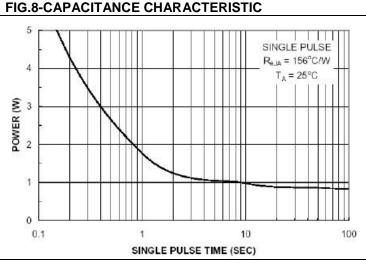
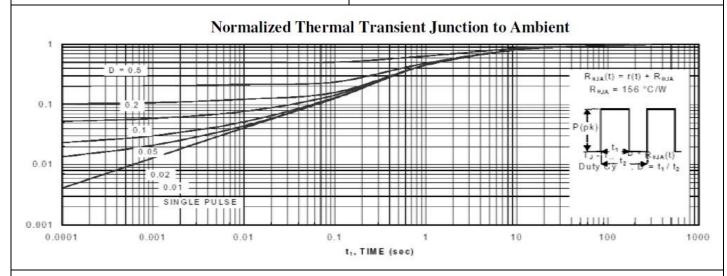


FIG.9-MAXIMUM SAFE OPERATING AREA

FIG.10-SINGLE PULSE MAXIMUM POWER DISSIPATION





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